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**ORIGINAL RESEARCH ARTICLE** 

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# STRUCTURAL AND OPTICAL PROPERTIES OF TITANIUM DIOXIDE THIN FILM DEPOSITED BYSPIN-COATING TECHNIQUE

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#### **ABSTRACT**

This research investigates the effects of thermal annealing on the optical, morphological and structural properties of Tio<sub>2</sub> thin film. Tio<sub>2</sub> was deposited on glass substrate by spin –coating technique using spin –coater model laurel WS-650Hz-23NPP. Surface morphology of thin film was studied using Scanning Electron Microscope (SEM) model ASPEX 3020. The optical absorbance and transmittance measurements were recorded by using a single beam spectrophotometer Avantes model Avalight-DH-5-BAL. After annealing at different temperature for one hour from 100°C to 550°C with Carbolite tubular oven model Srw 21-501042 Type-CT17, the morphology, optical properties of TiO<sub>2</sub> thin film were obtained. Observation showed that as the annealing temperature increases there is increase in absorption of photon energy and as the wavelength increases the absorption decreases. It also shows that transmittance increases as the wavelength increases and decreases with increases in annealing temperature. SEM reveal as annealing temperature increases, the grain size of Tio<sub>2</sub> gradually increases. The energy gap was observed and determined, the band gap energy decreases from 3.3 eV to 3.05eV as the annealing temperature increases. The impact of heat treatment of TiO<sub>2</sub> thin-film on the microstructure, surface roughness, photon absorption, and the band gap energy was obtained.

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#### INTRODUCTION

Titanium dioxide (TiO<sub>2</sub>) is the most investigated crystalline oxide in the surface science of metal oxides. Its physical and chemical properties are dominantly determined by its surface condition. Titanium dioxide has been studied extensively in the field of surface science due to the wide range of its applications and the expectation for insights into surface properties on the fundamental level (Diebold, 2003 and Liu, 2003). TiO<sub>2</sub> is a photocatalyst with relatively high efficiency, high transparency, excellent mechanically and chemically durable in the visible and near infrared region of spectrum. Titanium dioxide (TiO<sub>2</sub>) is a white solid inorganic substance that is thermally stable and non-flammable. It is chemically inert. Titanium dioxide has high corrosive resistance, excellent optical transparency in visible and near infrared regions as well as high refractive index (Bakar, 2014;

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Abdullah, 2015 and Wu, 2014). Kurniawan Foe *et al.*, (2014) fabricated a poly [3-hexylthiophene] (P3HT) and [6,6]-phenyl-C61-butyric acid methyl ester (PC $_{61}$ BM) organic photovoltaic cells (OPCs) using TiOx interfacial layer. Improvement in the photon absorption of the active layer was reported using TiO $_{x}$ layer coated organic photovoltaic solar cells (Kurniawan, 2014; Ourahmoun, 2010; Ilican, 2008).

#### EXPERIMENTAL PROCEDURES

# **Substrate preparation**

Glass slides of dimensions25.4mm by76.2mm was rinsed in de-ionized (DI) water. They were then placed in a beaker containing isopropyl (IPA) before cleaning in VWR ultrasonic cleaner with Digital Timer and heater 97043-986 at room temperature for30 min. The cleaned glass slides were dipped in ethanol and dried in a stream of nitrogen gas (N<sub>2</sub>). All glass slides received the same cleaning process.

# Preparation of Tio2 solution

25ml Ethanol solvent was added into 3g of Tio<sub>2</sub> powder from Sigma Aldrich. The solution then underwent ageing process for 3 hours upon sonication at room temperature without heat to allow homogeneous mixture and Tio<sub>2</sub> powder to fully dilute into solvent. Ethanol was chosen as a solvent because it has no characteristic absorption and emission in the visible range.

#### Film processing and Deposition

Thin films were obtained by spin coatingthe solution of Tio<sub>2</sub> dropped onto the pre-cleaned glass substrate placed on the stub of the spin –coater model laurel WS-650Hz-23NPP.Which was rotated at 4000 rpm for 30 sec atroom temperature. After depositing by spin coating, the films were dried at 60°C for 30 min in an oven model Uniscope SM 9063 Laboratory oven SURGIFRIEND MEDICALS, England to evaporate the solvent. The process from coating to drying was repeated to obtain the desired thickness of the film. Filmswere annealed at different temperatures ranging from 100°C to 550°C for 1hr with Carbolite tubular oven model Srw 21-501042 Type-CT17 and quenched to room temperature in argon gasto study the effect of annealing. One sample was not subjected to heat treatment after the initial pre-heating at 60°C for 30 min which depict control.

#### **Optical Characterization**

The optical transmittance of the samples was measured and recorded with Avantes UV-VIS spectrophotometer model Avalight-DH-5-BAL. The spectrophotometer operates by providing a light source towards an aperture using an optical fiber and uses another aperture to measure the amount of light transmitted or reflected by the sample under test. The transmittance spectrum is as shown in figure 1&2 The absorption spectra for Tio<sub>2</sub> thin films annealed at different temperatures is as shown in figure 3 It is deduced that as the annealing temperature increases there is increase in absorption of photon energy. It also shows that transmission increases as the wavelength increases and decreases with increases in annealing temperature. As the annealing temperature increases the absorption increases and as the wavelength increases the absorption decreases. To convert between the absorbance and transmittance, equation (1) was used.

Absorbance (A) =2- 
$$\log_{10.0\%T}$$
 (1)

The absorption coefficient of thin film is calculated from the formula (2) [9]

$$\alpha = 2.303(A/t) \tag{2}$$

Where, A is absorbance and t is the thickness (Shakti, 2010). The absorption coefficient  $\alpha$  and the extinction coefficient k are related by the formula (3)

$$K = \alpha \lambda / 4\pi, K = 2.303(A/t) \lambda / 4\pi$$
(3)

Extinction coefficient k is calculated with this formula  $K=2.303(A/t) \, \lambda/4\pi$ 

Where,  $\lambda$  is the wavelength. The variation of extinction coefficient k with wavelength is shown in figure 4. Tio<sub>2</sub> is a direct –gap semiconductor. The optical band gap energy Eg

and absorption coefficient  $\alpha$  is related by the equation (4) (Tauc, 1970; Hussein, 2011; Balogun, 2017).

$$(\alpha h v)^2 = h v - Eg \tag{4}$$

Where, $\alpha$  is the absorption coefficient and hv is the incident photon energy. Band Gap Energy (E) = hc/ $\lambda$  where h = planks constant =6.626 x 10<sup>-34</sup> joules sec. C= speed of light =3.0 x 10<sup>8</sup> meter/sec. where lev =1.6 x 10<sup>-19</sup> joules (conversion factor). For calculation of the optical band gap of films, the curve of  $(\alpha hv)^2$  vs. hv was plotted. The energy band gap was obtained from straight line plot of  $(\alpha hv)^2$  vs. hv by extrapolating of the line to base line in Figure 7 to Figure 10.

## **Optical transmittance measurement**

The optical transmittance of the samples was measured with spectrophotometer Avantes model Avalight-DH-5-BAL.

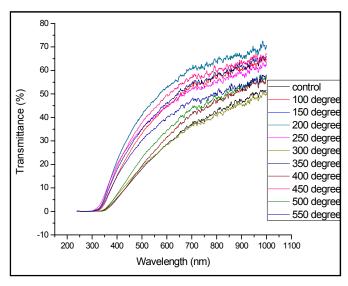


Figure 1. Plot of Transmittance vs Wavelength graph

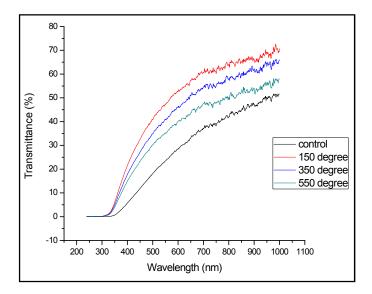


Figure 2. Plot of selected Temperatures of Transmittance vs Wavelength graph

# Optical reflectance measurement

The optical reflectance of the samples was measured with Avantes UV-VIS spectrophotometer model Avalight-DH-5-BAL. The plot of reflectance versus wavelength is shown in Figure 5 and Figure 6.

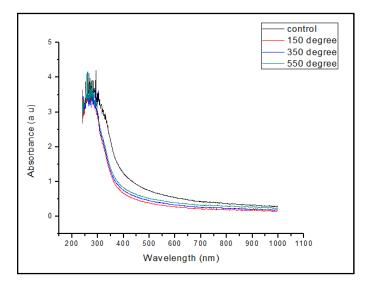


Figure 3. Plot of selected Temperatures of Absorbance vs Wavelength graph

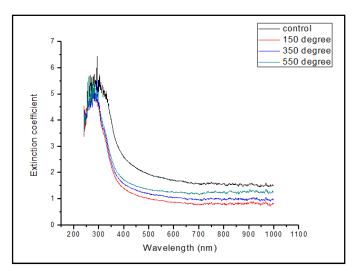


Figure 4. Plot of Extinction coefficient vs Wavelength graph

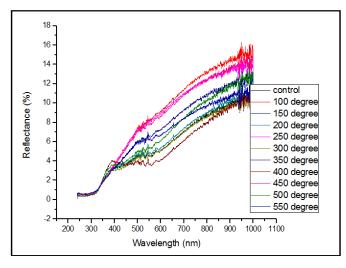


Figure 5. Plot of Reflectance vs Wavelength graph

## Morphological Characterization

Scanning electron microscope (SEM) model ASPEX 3020 was employed to image the surface of the samples. All samples were appropriately cut to a size that can fit on the specimen stub of the SEM machine. SEM provides a useful means for

investigating the morphological properties of the samples surface at desired magnification. SEM morphology study of samples was carried out to analyze the surface behavior.

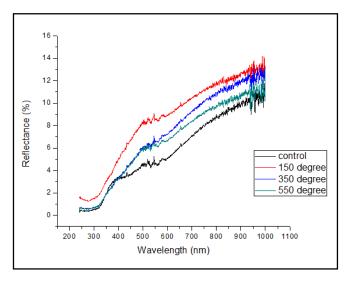


Figure 6. Plot of selected Temperatures of Reflectance vs Wavelength graph

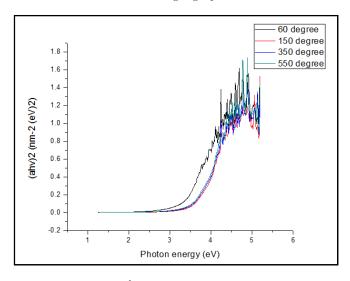


Figure 7. Plot of  $(\alpha hv)^2$  versus hv for Tio<sub>2</sub> thin films annealed at different temperature

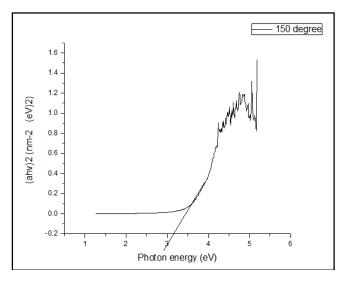


Figure 8. Plot of (αhv)<sup>2</sup>versus hv for Tio<sub>2</sub> thin film annealed at 150°c

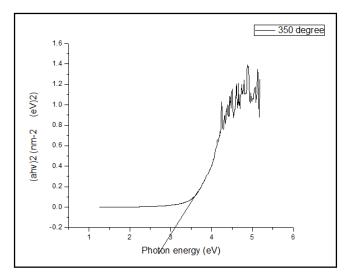


Figure 9. Plot of (αhv)<sup>2</sup>versus hv for Tio<sub>2</sub> thin film annealed at 350<sup>0</sup>c

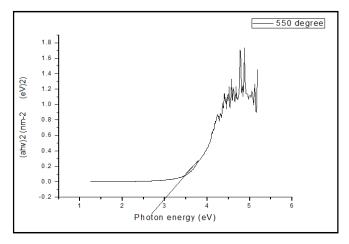


Figure 10. Plot of  $(\alpha hv)^2$ versus hv for Tio $_2$  thin film annealed at  $550^0c$ 

Figure 11 to Figure 14 shows images at different temperature in order to compare their surface morphologies with respect to the temperature variation. Observation showed that as the annealing temperature is increased the surface roughness increases. This may be due to increase in grain size with increase in annealing temperature. Figure 11 to figure 14 shows the morphological images at control,  $150^{\circ}$ C,  $350^{\circ}$ C,  $550^{\circ}$ C

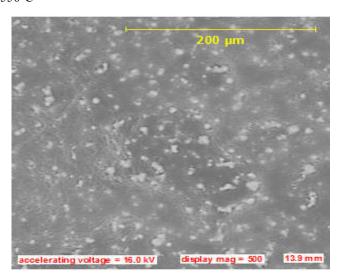


Figure 11. SEM image of  $Tio_2$  control

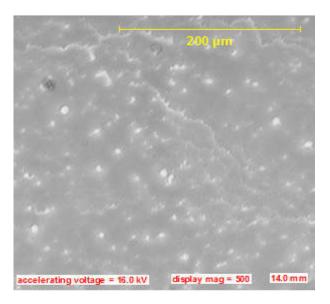


Figure 12. SEM image of Tio<sub>2</sub> at 150<sup>0</sup>C

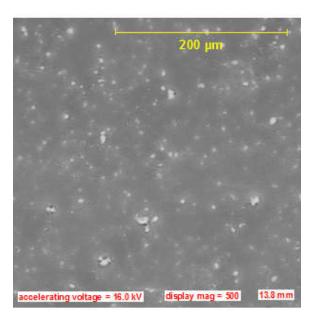


Figure 13. SEM image of Tio<sub>2</sub> at 350<sup>o</sup>C

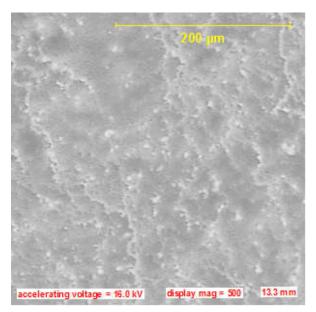


Figure 14. SEM image of Tio<sub>2</sub> at 550<sup>0</sup>C

### **RESULTS**

It was deduced that as the annealing temperature increases there is increase in absorption of photon energy. It also shows that transmission increases as the wavelength increases and decreases with increases in annealing temperature. As the annealing temperature increases the absorption increases and as the wavelength increases the absorption decreases. Titanium dioxide thin films prepared on glass substrate by spin coating process and annealed at different temperatures from 100°C to 550°C step of 50°C. It was deduced that annealing temperature affects the morphological and optical properties of the Tio<sub>2</sub> thin films. The transmission spectrums of the films were Spectrophotometer. recorded by UV-VIS Extinction coefficients were calculated. The extinction coefficient showed some variation with rise in annealing temperature of Tio2 films. The Optical energy band gap values were obtained by plot of  $(\alpha h v)^2$  versus hv. The value of band gaps agrees approximately with that of bulk Tio<sub>2</sub>. As the annealing temperature increases the band gap value decreases. SEM image of the samples revealed that the roughness of the surface of the sampleincreases annealing temperature increases, this is attributed to increase in grain size, so that band gap energydecreases.

## **DISCUSSION**

Unheated sample (control) has the least percent transmittance compared to the heated samples at  $100^{\circ}$ C to  $550^{\circ}$ C. Unannealed sample has the highest absorbance in the visible spectrum and near infrared spectrum compared to the thermally annealed samples and it also has the highest extinction coefficient value. But has the least band gap energy approximately 2.8eV compared to annealed samples. SEM analysis showed that surface roughness of unheated sample is the highest.

#### Conclusion

The Titanium dioxide thin film was deposited and annealed at 100°C to 550°C in step of 50°C, respectively. The result shows that the film annealed at 550°C has the highest absorption in the visible region. The unheated sample (control) has the highest extinction coefficient value but has the least band gap energy. The band gap energy of the thin filmdecreases as the annealing temperature increases. As the annealing temperature increases the band gap energy value decreases from 3.3 eV to 3.05eV. SEM image of the samples revealed that the roughness of the surface of the thinfilmincreases as annealing temperature increases, this is attributed to increase in grain size, so that band gap energy decreases. Heat treatment will improve the stability or efficiency of Tio<sub>2</sub> thin film.

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